TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

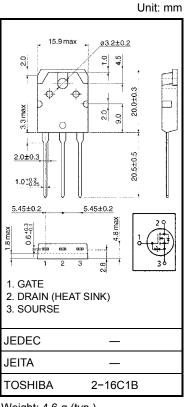
2SK2744

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance: $RDS(ON) = 15 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 27 \text{ S (typ.)}$
- Low leakage current: $I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 50 \ V)$
- Enhancement mode: $V_{th} = 1.5 \sim 3.5 \text{ V} (V_{DS} = 10 \text{ V}, \text{I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	50	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	50	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	45	А	
	Pulse (Note 1)	I _{DP}	180	A	
Drain power dissipation	n (Tc = 25°C)	PD	125	W	
Single pulse avalanche energy (Note 2)		E _{AS}	95	mJ	
Avalanche current		I _{AR}	45	А	
Repetitive avalanche energy (Note 3)		E _{AR}	12.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.0	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 25 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$ (initial), L = 58 μ H, R_G = 25 Ω , I_{AR} = 45 A

Note 3: Repetitive rating: pulse width limited by maximum junction temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

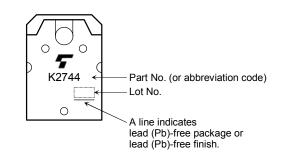
Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μA
Drain cut-off current		I _{DSS}	$V_{DS} = 50 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	100	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	50	_	_	V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	1.5	_	3.5	V
Drain-source ON resistance		R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 25 \text{ A}$		15	20	mΩ
Forward transfer admittance		Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 25 \text{ A}$	15	27		S
Input capacitance		C _{iss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	_	2300		pF
Reverse transfer capacitance		C _{rss}			420		pF
Output capacitance		C _{oss}	1		1200		pF
Switching time	Rise time	t _r	$V_{GS}^{10 V} \qquad I_D = 25 A \\ V_{GS}^{0 V} \qquad G \\ V_{DD} \simeq 25 V$		30	_	
	Turn-on time	t _{on}		_	45	_	
	Fall time	t _f		_	80	_	ns
	Turn-off time	t _{off}	Duty \leq 1%, t _w = 10 μ s	_	230	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	68	_	nC
Gate-source charge		Q _{gs}	$V_{DD} \simeq 40$ V, $V_{GS} = 10$ V, $I_D = 45$ A	_	20	_	nC
Gate-drain ("miller") charge		Q _{gd}	1	_	48	_	nC

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	45	А
Pulse drain reverse current (Note 1)	I _{DRP}	_		_	180	А
Forward voltage (diode)	V _{DSF}	$I_{DR} = 45 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.8	V
Reverse recovery time	t _{rr}	$I_{DR}=45~\text{A},~\text{V}_{GS}=0~\text{V}$		130	_	ns
Reverse recovery charge	Qrr	$dI_{DR}/dt = 50 \text{ A}/\mu \text{s}$		0.3	_	μC

Marking



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